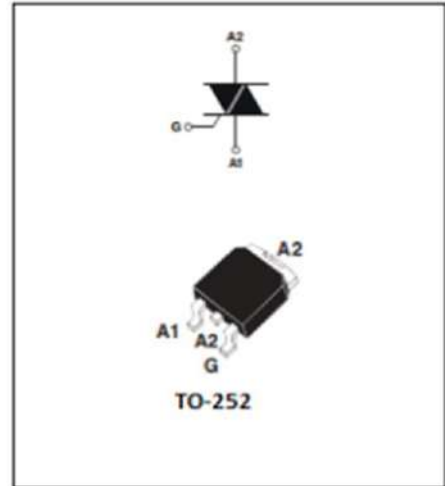


YZPST-BT134Series 2A TRIACs
DESCRIPTION:

The BT134 triac series is suitable to fit all models of control Found in applications such as motor control ,industrial and domestic lighting ,heating and static switching , motor speed controllers,...

Different gate current sensitivities are available, allowing optimized performances when controlled directly from microcontrollers. UL approved.


MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	2	A
V_{DRM} V_{RRM}	600	V
V_{TM}	1.55	V

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40 ~150	°C
Operating junction temperature range	T_j	-40~125	°C
Repetitive peak off-state voltage (T =25°C)	V_{DRM}	600	V
Repetitive peak reverse voltage (T =25°C)	V_{RRM}	600	V
RMS on-state current (T =105°C)	$I_{T(RMS)}$	2	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I_{TSM}	20	A
I^2t value for fusing (tp=10ms)	I^2t	5.1	A ² S
Critical rate of rise of on-state current (I =2 ×I _{GT})	dI/dt	50	A/μS
Peak gate current	I_{GM}	1	A
Average gate power dissipation	$P_{G(AV)}$	0.1	W

ELECTRICAL CHARACTERISTICS (T=25°C unless otherwise specified)
4 Quadrants

Symbol	Test Condition	Quadrant		Value	Unit
I_{GT}	$V = 12V$ $R = 33\Omega$	I II III	MAX.	10	mA
		IV		20	
V_{GT}		I II III IV	MAX.	1.3	V
V_{GD}	$V_D = V_{DRM}$ $T_j = 125^\circ C$ $R = 3.3K\Omega$	I II III IV	MIN.	0.2	V
I_L	$I_G = 1.2I_{GT}$	I III IV	MAX.	20	mA
		II		30	
I_H	$I_T = 100mA$		MAX.	15	mA
dV/dt	$V_D = 2/3V_{DRM}$ Gate Open $T_j = 125^\circ C$		MIN.	40	V/ μs

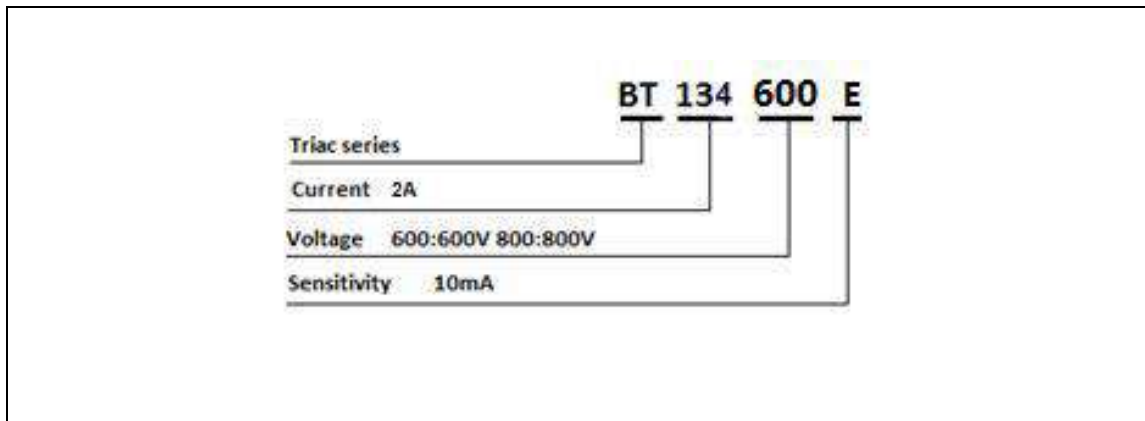
STATIC CHARACTERISTICS

Symbol	Parameter		Value	Unit
V_{TM}	$I_{TM} = 5.5A$ $t_p = 380\mu s$	$T_j = 25^\circ C$	1.55	V
I_{DRM}	$V_D = V_{DRM}$ $V_R = V_{RRM}$	$T_j = 25^\circ C$	5	μA
I_{RRM}		$T_j = 125^\circ C$	1	mA

Thermal Resistances

Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	junction to ambient	70	$^\circ C/W$
$R_{th(j-c)}$	Junction to case(AC)	2.6	

Ordering Information Scheme



TO-252 Package Mechanical Data

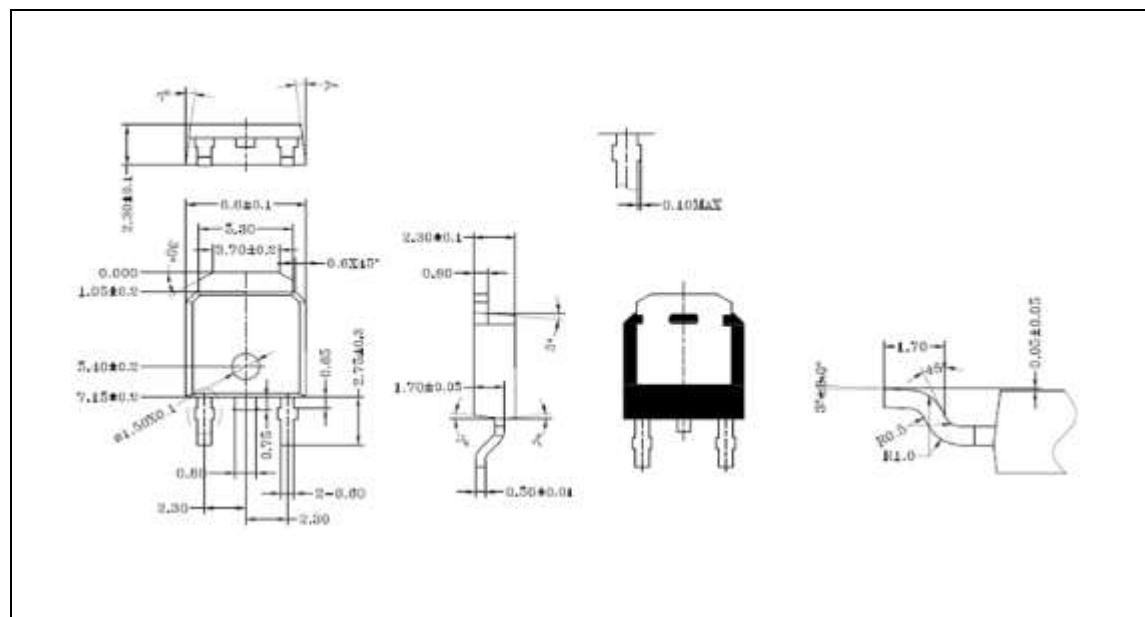


FIG.1 Maximum power dissipation versus RMS on-state current

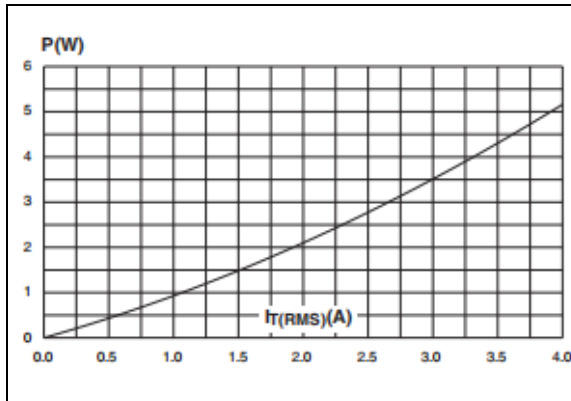


FIG.2: RMS on-state current versus case temperature

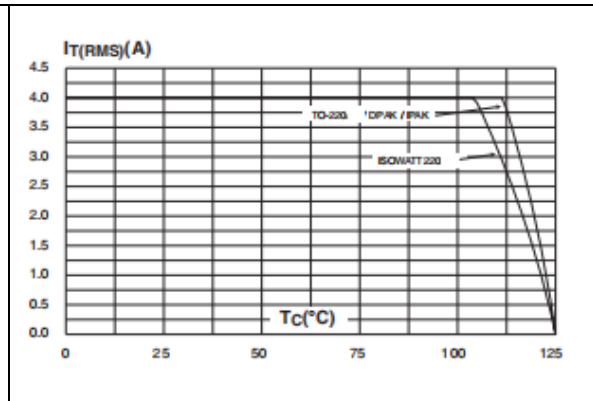


FIG.3: Surge peak on-state current versus number of cycles

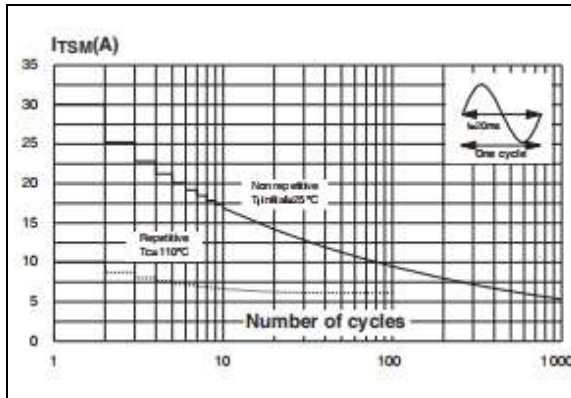


FIG.4: On-state characteristics (maximum values)

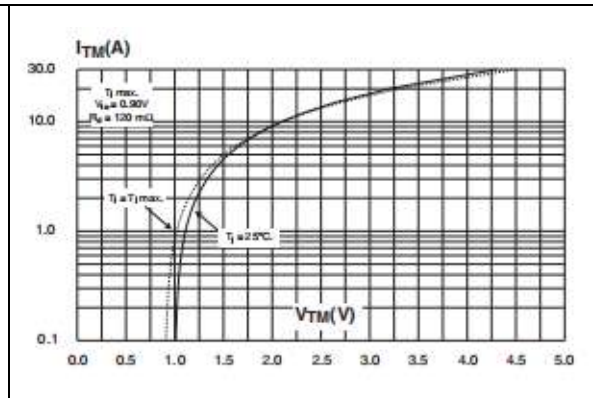


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20ms$, and corresponding value of $I^2 t$ ($dI/dt < 50A/\mu s$)

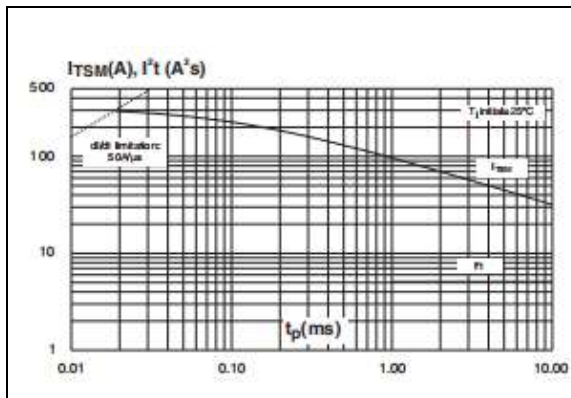


FIG.6: Relative variations of gate trigger current holding current and latching current versus junction temperature

